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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	•
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101lgafb-x0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

(5/12)

Pin	Package	Data	Fields of	Ordering Part Number
count		flash	Application	
			Note	
48 pins	48-pin plastic	Mounted	Α	R5F100GAAFB#V0, R5F100GCAFB#V0, R5F100GDAFB#V0,
	LFQFP ( $7 \times 7$ mm,			R5F100GEAFB#V0, R5F100GFAFB#V0, R5F100GGAFB#V0,
	0.5 mm pitch)			R5F100GHAFB#V0, R5F100GJAFB#V0, R5F100GKAFB#V0,
				R5F100GLAFB#V0
				R5F100GAAFB#X0, R5F100GCAFB#X0, R5F100GDAFB#X0,
				R5F100GEAFB#X0, R5F100GFAFB#X0, R5F100GGAFB#X0,
				R5F100GHAFB#X0, R5F100GJAFB#X0, R5F100GKAFB#X0,
				R5F100GLAFB#X0
			D	R5F100GADFB#V0, R5F100GCDFB#V0, R5F100GDDFB#V0,
				R5F100GEDFB#V0, R5F100GFDFB#V0, R5F100GGDFB#V0,
				R5F100GHDFB#V0, R5F100GJDFB#V0, R5F100GKDFB#V0,
				R5F100GLDFB#V0
				R5F100GADFB#X0, R5F100GCDFB#X0, R5F100GDDFB#X0,
				R5F100GEDFB#X0, R5F100GFDFB#X0, R5F100GGDFB#X0,
				R5F100GHDFB#X0, R5F100GJDFB#X0, R5F100GKDFB#X0,
				R5F100GLDFB#X0
			G	R5F100GAGFB#V0, R5F100GCGFB#V0, R5F100GDGFB#V0,
				R5F100GEGFB#V0, R5F100GFGFB#V0, R5F100GGGFB#V0,
				R5F100GHGFB#V0, R5F100GJGFB#V0
				R5F100GAGFB#X0, R5F100GCGFB#X0, R5F100GDGFB#X0,
				R5F100GEGFB#X0, R5F100GFGFB#X0, R5F100GGGFB#X0,
				R5F100GHGFB#X0, R5F100GJGFB#X0
		Not	Α	R5F101GAAFB#V0, R5F101GCAFB#V0, R5F101GDAFB#V0,
		mounted		R5F101GEAFB#V0, R5F101GFAFB#V0, R5F101GGAFB#V0,
				R5F101GHAFB#V0, R5F101GJAFB#V0, R5F101GKAFB#V0,
				R5F101GLAFB#V0
				R5F101GAAFB#X0, R5F101GCAFB#X0, R5F101GDAFB#X0,
				R5F101GEAFB#X0, R5F101GFAFB#X0, R5F101GGAFB#X0,
				R5F101GHAFB#X0, R5F101GJAFB#X0, R5F101GKAFB#X0,
				R5F101GLAFB#X0
			D	R5F101GADFB#V0, R5F101GCDFB#V0, R5F101GDDFB#V0,
				R5F101GEDFB#V0, R5F101GFDFB#V0, R5F101GGDFB#V0,
				R5F101GHDFB#V0, R5F101GJDFB#V0, R5F101GKDFB#V0,
				R5F101GLDFB#V0
				R5F101GADFB#X0, R5F101GCDFB#X0, R5F101GDDFB#X0,
				R5F101GEDFB#X0, R5F101GFDFB#X0, R5F101GGDFB#X0,
1				R5F101GHDFB#X0, R5F101GJDFB#X0, R5F101GKDFB#X0,
				R5F101GLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(8/12)

Pin count	Package	Data flash	Fields of	Ordering Part Number
			Application Note	
64 pins	64-pin plastic LQFP	Mounted	Α	R5F100LCAFA#V0, R5F100LDAFA#V0,
	(12 × 12 mm, 0.65			R5F100LEAFA#V0, R5F100LFAFA#V0,
	mm pitch)			R5F100LGAFA#V0, R5F100LHAFA#V0,
				R5F100LJAFA#V0, R5F100LKAFA#V0, R5F100LLAFA#V0
				R5F100LCAFA#X0, R5F100LDAFA#X0,
				R5F100LEAFA#X0, R5F100LFAFA#X0,
			D	R5F100LGAFA#X0, R5F100LHAFA#X0,
				R5F100LJAFA#X0, R5F100LKAFA#X0, R5F100LLAFA#X0
				R5F100LCDFA#V0, R5F100LDDFA#V0,
				R5F100LEDFA#V0, R5F100LFDFA#V0,
				R5F100LGDFA#V0, R5F100LHDFA#V0,
				R5F100LJDFA#V0, R5F100LKDFA#V0, R5F100LLDFA#V0
			G	R5F100LCDFA#X0, R5F100LDDFA#X0,
				R5F100LEDFA#X0, R5F100LFDFA#X0,
				R5F100LGDFA#X0, R5F100LHDFA#X0,
				R5F100LJDFA#X0, R5F100LKDFA#X0, R5F100LLDFA#X0
				R5F100LCGFA#V0, R5F100LDGFA#V0,
				R5F100LEGFA#V0, R5F100LFGFA#V0
				R5F100LCGFA#X0, R5F100LDGFA#X0,
				R5F100LEGFA#X0, R5F100LFGFA#X0
				R5F100LGGFA#V0, R5F100LHGFA#V0,
				R5F100LJGFA#V0
				R5F100LGGFA#X0, R5F100LHGFA#X0,
				R5F100LJGFA#X0
		Not	Α	R5F101LCAFA#V0, R5F101LDAFA#V0,
		mounted		R5F101LEAFA#V0, R5F101LFAFA#V0,
				R5F101LGAFA#V0, R5F101LHAFA#V0,
				R5F101LJAFA#V0, R5F101LKAFA#V0, R5F101LLAFA#V0
				R5F101LCAFA#X0, R5F101LDAFA#X0,
				R5F101LEAFA#X0, R5F101LFAFA#X0,
			D	R5F101LGAFA#X0, R5F101LHAFA#X0,
				R5F101LJAFA#X0, R5F101LKAFA#X0, R5F101LLAFA#X0
				R5F101LCDFA#V0, R5F101LDDFA#V0,
				R5F101LEDFA#V0, R5F101LFDFA#V0,
				R5F101LGDFA#V0, R5F101LHDFA#V0,
				R5F101LJDFA#V0, R5F101LKDFA#V0, R5F101LLDFA#V0
				R5F101LCDFA#X0, R5F101LDDFA#X0,
				R5F101LEDFA#X0, R5F101LFDFA#X0,
				R5F101LGDFA#X0, R5F101LHDFA#X0,
				R5F101LJDFA#X0, R5F101LKDFA#X0, R5F101LLDFA#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



Table 1-1. List of Ordering Part Numbers

(10/12)

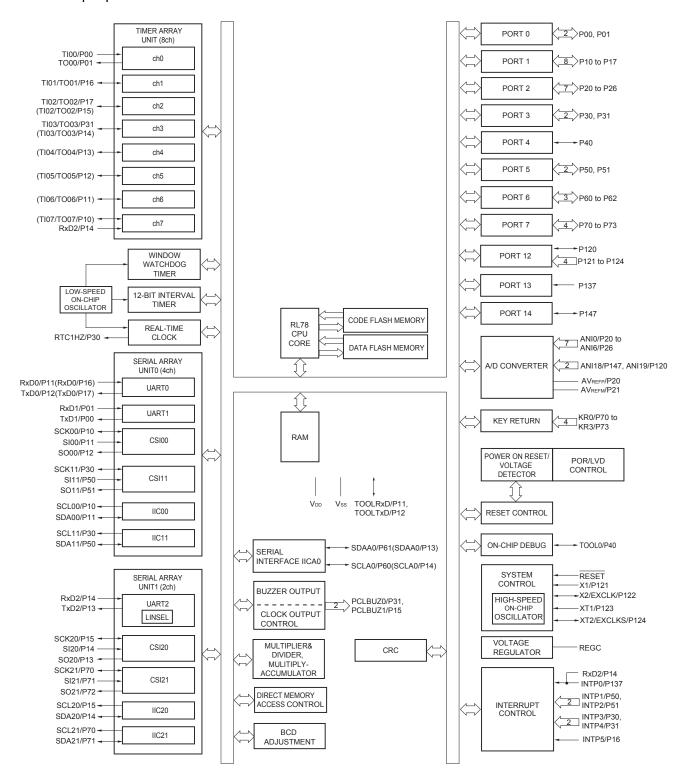
Pin count	Package	Data flash	Fields of Application	Ordering Part Number
80 pins	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	Mounted	А	R5F100MFAFA#V0, R5F100MGAFA#V0, R5F100MHAFA#V0, R5F100MJAFA#V0, R5F100MKAFA#V0, R5F100MLAFA#V0 R5F100MFAFA#X0, R5F100MGAFA#X0, R5F100MHAFA#X0, R5F100MJAFA#X0, R5F100MKAFA#X0, R5F100MLAFA#X0
			D	R5F100MFDFA#V0, R5F100MGDFA#V0, R5F100MHDFA#V0, R5F100MJDFA#V0, R5F100MKDFA#V0, R5F100MFDFA#X0, R5F100MFDFA#X0, R5F100MFDFA#X0, R5F100MJDFA#X0, R5F100MKDFA#X0, R5F100MLDFA#X0
			G	R5F100MFGFA#V0, R5F100MGGFA#V0, R5F100MHGFA#V0, R5F100MJGFA#V0 R5F100MFGFA#X0, R5F100MGGFA#X0, R5F100MJGFA#X0, R5F100MJGFA#X0
		Not mounted	A	R5F101MFAFA#V0, R5F101MGAFA#V0, R5F101MHAFA#V0, R5F101MJAFA#V0, R5F101MKAFA#V0, R5F101MLAFA#V0 R5F101MFAFA#X0, R5F101MGAFA#X0, R5F101MJAFA#X0, R5F101MKAFA#X0, R5F101MLAFA#X0
			D	R5F101MFDFA#V0, R5F101MGDFA#V0, R5F101MHDFA#V0, R5F101MJDFA#V0, R5F101MKDFA#V0, R5F101MLDFA#V0 R5F101MFDFA#X0, R5F101MGDFA#X0, R5F101MHDFA#X0, R5F101MJDFA#X0, R5F101MKDFA#X0, R5F101MJDFA#X0
	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	Mounted	A	R5F100MFAFB#V0, R5F100MGAFB#V0, R5F100MHAFB#V0, R5F100MJAFB#V0, R5F100MKAFB#V0, R5F100MLAFB#V0 R5F100MFAFB#X0, R5F100MGAFB#X0, R5F100MJAFB#X0, R5F100MKAFB#X0, R5F100MLAFB#X0
			D	R5F100MFDFB#V0, R5F100MGDFB#V0, R5F100MHDFB#V0, R5F100MJDFB#V0, R5F100MKDFB#V0, R5F100MLDFB#V0 R5F100MFDFB#X0, R5F100MGDFB#X0, R5F100MHDFB#X0, R5F100MJDFB#X0, R5F100MKDFB#X0, R5F100MLDFB#X0
			G	R5F100MFGFB#V0, R5F100MGGFB#V0, R5F100MHGFB#V0, R5F100MJGFB#V0 R5F100MFGFB#X0, R5F100MGGFB#X0, R5F100MJGFB#X0, R5F100MJGFB#X0
		Not mounted	А	R5F101MFAFB#V0, R5F101MGAFB#V0, R5F101MHAFB#V0, R5F101MJAFB#V0, R5F101MKAFB#V0, R5F101MFAFB#X0, R5F101MGAFB#X0, R5F101MHAFB#X0, R5F101MJAFB#X0, R5F101MKAFB#X0, R5F101MLAFB#X0
			D	R5F101MFDFB#V0, R5F101MGDFB#V0, R5F101MHDFB#V0, R5F101MJDFB#V0, R5F101MKDFB#V0, R5F101MLDFB#V0 R5F101MFDFB#X0, R5F101MGDFB#X0, R5F101MHDFB#X0, R5F101MJDFB#X0, R5F101MKDFB#X0, R5F101MLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



### 1.5.7 40-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

**3.** The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see **6.9.3 Operation as multiple PWM output function** in the RL78/G13 User's Manual).

4. When setting to PIOR = 1

11	<b>n</b>	n	١
14	ر2	_	ı

Ite	Item		20-pin 24-pin		25-pin		30-pin		32-pin		36-pin		
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Clock output/buzze	er output		_		1		1		2		2		2
				88 kHz, 9 n clock: f				ИHz, 5 N	IHz, 10 N	МНz		•	
8/10-bit resolution	A/D converter	6 chanr	nels	6 chanı	nels	6 chanı	nels	8 chan	nels	8 chan	nels	8 chan	nels
Serial interface		[20-pin,	24-pin,	25-pin p	roducts]								
		• CSI:	1 chann	el/simpli	fied I <sup>2</sup> C:	1 channe	el/UART	: 1 chanı	nel				
		• CSI:	1 chann	el/simpli	fied I <sup>2</sup> C:	1 channe	el/UART	: 1 chanı	nel				
		[30-pin,	32-pin <sub> </sub>	products	]								
		• CSI:	1 chann	el/simplit el/simplit el/simplit	fied I <sup>2</sup> C:	1 channe	el/UART	: 1 chanı	nel	ng LIN-bi	us): 1 ch	annel	
		[36-pin	products	s]									
		<ul> <li>CSI: 1 channel/simplified I<sup>2</sup>C: 1 channel/UART: 1 channel</li> <li>CSI: 1 channel/simplified I<sup>2</sup>C: 1 channel/UART: 1 channel</li> <li>CSI: 2 channels/simplified I<sup>2</sup>C: 2 channels/UART (UART supporting LIN-bus): 1 channel</li> </ul>											
	I <sup>2</sup> C bus			1 chanı		1 chanı		1 chan		1 chan		1 chan	nel
Multiplier and divid	der/multiply-	<ul> <li>16 bits × 16 bits = 32 bits (Unsigned or signed)</li> <li>32 bits ÷ 32 bits = 32 bits (Unsigned)</li> <li>16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)</li> </ul>											
DMA controller		2 chanr	nels										
Vectored interrupt	Internal	2	23	2	24	2	24	2	27	2	27	2	27
sources	External	;	3		5		5		6		6		6
Key interrupt		_											
Reset		<ul><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li></ul>	nal reset nal reset nal reset nal reset	by watch by power by volta by illegate by RAM	er-on-res ge detec al instruc I parity e	set ctor tion exec rror		e					
Power-on-reset cir	cuit	<ul> <li>Internal reset by illegal-memory access</li> <li>Power-on-reset: 1.51 V (TYP.)</li> <li>Power-down-reset: 1.50 V (TYP.)</li> </ul>											
Voltage detector	<ul> <li>Rising edge: 1.67 V to 4.06 V (14 stages)</li> <li>Falling edge: 1.63 V to 3.98 V (14 stages)</li> </ul>												
On-chip debug fun	ection	Provide	ed										
Power supply volta	age	V <sub>DD</sub> = 1	.6 to 5.5	V (T <sub>A</sub> =	-40 to +8	35°C)							
		$V_{DD} = 2$	4 to 5.5	V (T <sub>A</sub> = -	40 to +1	05°C)							
Operating ambient	t temperature			C (A: Co i°C (G: Ir				ndustria	l applica	tions )			
		14 - 40	10 T 100	. o (a. 11	idudilidi	αργιισατι	0110)						

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

#### 2.3 DC Characteristics

### 2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$ 

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high <sup>Note 1</sup>		Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$1.6~V \le EV_{DD0} \le 5.5~V$			-10.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			-55.0	mA
		P125 to P127, P130, P140 to P145	$2.7~V \leq EV_{DD0} < 4.0~V$			-10.0	mA
			$1.8~V \leq EV_{DD0} < 2.7~V$			-5.0	mA
		,	$1.6~V \leq EV_{DD0} < 1.8~V$			-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31,				-80.0	mA
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to	$2.7~V \leq EV_{DD0} < 4.0~V$			-19.0	mA
		P117, P146, P147	$1.8~V \leq EV_{DD0} < 2.7~V$			-10.0	mA
		(When duty $\leq 70\%$ Note 3)	$1.6~V \leq EV_{DD0} < 1.8~V$			-5.0	mA
	Total of all pins (When duty ≤ 70% Note 3)	$1.6~V \leq EV_{DD0} \leq 5.5~V$			-135.0 Note 4	mA	
	<b>І</b> он2	Per pin for P20 to P27, P150 to P156	$1.6~V \leq V_{DD} \leq 5.5~V$			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	$1.6~V \leq V_{DD} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV<sub>DD0</sub>, EV<sub>DD1</sub>, V<sub>DD</sub> pins to an output pin.
  - 2. However, do not exceed the total current value.
  - 3. Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins =  $(IOH \times 0.7)/(n \times 0.01)$ 

<Example> Where n = 80% and loh = -10.0 mA

Total output current of pins =  $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$  mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

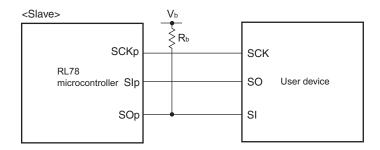
**4.** The applied current for the products for industrial application (R5F100xxDxx, R5F101xxDxx, R5F100xxGxx) is -100 mA.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



### CSI mode connection diagram (during communication at different potential)



- Remarks 1.  $R_b[\Omega]$ :Communication line (SOp) pull-up resistance,  $C_b[F]$ : Communication line (SOp) load capacitance,  $V_b[V]$ : Communication line voltage
  - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
  - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
  - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

**Notes 1.** The first clock pulse is generated after this period when the start/restart condition is detected.

<R>

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

**Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode:  $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ 



(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{\text{DD}}, \text{Reference voltage (-)} = \text{V}_{\text{SS}})$ 

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$		1.2	±7.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI0 to ANI14,	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
		ANI16 to ANI26	$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μS
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μS
Zero-scale error <sup>Notes 1, 2</sup>	Ezs	1	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±0.85	%FSR
Full-scale error <sup>Notes 1, 2</sup>	Ers	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±0.85	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±4.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±6.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
			$1.6~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$ Note 3			±2.5	LSB
Analog input voltage	Vain	ANI0 to ANI14		0		V <sub>DD</sub>	٧
		ANI16 to ANI26		0		EV <sub>DD0</sub>	٧
		Internal reference voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (hi	gh-speed main) mode)		V <sub>BGR</sub> Note 4		V
		Temperature sensor output (2.4 V ≤ VDD ≤ 5.5 V, HS (hi	-		VTMPS25 Note 4	1	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When the conversion time is set to 57  $\mu$ s (min.) and 95  $\mu$ s (max.).
- 4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

## LVD Detection Voltage of Interrupt & Reset Mode

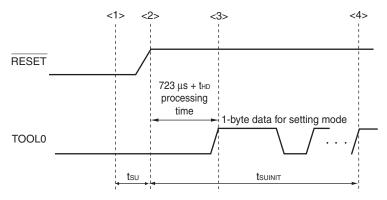
(Ta = -40 to +85°C, VPDR  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V)

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V <sub>LVDA0</sub>	V <sub>POC2</sub> ,	VPOC1, VPOC0 = 0, 0, 0	, falling reset voltage	1.60	1.63	1.66	V
mode	VLVDA1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	٧
				Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	<b>V</b>
				Falling interrupt voltage	2.80	2.86	2.91	٧
	V <sub>LVDB0</sub>	V <sub>POC2</sub> ,	VPOC1, VPOC0 = 0, 0, 1	, falling reset voltage	1.80	1.84	1.87	V
	V <sub>LVDB1</sub>		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	>
				Falling interrupt voltage	1.90	1.94	1.98	٧
	VLVDB2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	٧
				Falling interrupt voltage	2.00	2.04	2.08	V
	V <sub>LVDB3</sub>		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V	
	V <sub>LVDC0</sub>	V <sub>POC2</sub> ,	VPOC1, VPOC0 = 0, 1, 0	, falling reset voltage	2.40	2.45	2.50	٧
	VLVDC1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	<b>V</b>
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	>
				Falling interrupt voltage	2.60	2.65	2.70	V
	V <sub>LVDC3</sub>		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	٧
				Falling interrupt voltage	3.60	3.67	3.74	V
	V <sub>LVDD0</sub>	V <sub>POC2</sub> ,	VPOC1, VPOC0 = 0, 1, 1	, falling reset voltage	2.70	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	<b>V</b>
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

### 2.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuіліт	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

**Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

# 3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications  $T_A = -40$  to +105°C R5F100xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
  - 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
  - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.
  - 4. Please contact Renesas Electronics sales office for derating of operation under  $T_A = +85^{\circ}C$  to  $+105^{\circ}C$ . Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13 is used in the range of  $T_A = -40$  to +85°C, see CHAPTER 2 ELECTRICAL SPECIFICATIONS ( $T_A = -40$  to +85°C).

There are following differences between the products "G: Industrial applications ( $T_A = -40$  to  $+105^{\circ}$ C)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Aŗ	oplication
	A: Consumer applications,     D: Industrial applications	G: Industrial applications
Operating ambient temperature	T <sub>A</sub> = -40 to +85°C	T <sub>A</sub> = -40 to +105°C
Operating mode Operating voltage range	HS (high-speed main) mode: $2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 32 \text{ MHz}$ $2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 16 \text{ MHz}$ $LS \text{ (low-speed main) mode:}$ $1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 8 \text{ MHz}$ $LV \text{ (low-voltage main) mode:}$ $1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 4 \text{ MHz}$	HS (high-speed main) mode only: $2.7~V \le V_{DD} \le 5.5~V @ 1~MHz~to~32~MHz$ $2.4~V \le V_{DD} \le 5.5~V @ 1~MHz~to~16~MHz$
High-speed on-chip oscillator clock accuracy	1.8 V $\leq$ V <sub>DD</sub> $\leq$ 5.5 V $\pm$ 1.0%@ T <sub>A</sub> = -20 to +85°C $\pm$ 1.5%@ T <sub>A</sub> = -40 to -20°C 1.6 V $\leq$ V <sub>DD</sub> $<$ 1.8 V $\pm$ 5.0%@ T <sub>A</sub> = -20 to +85°C $\pm$ 5.5%@ T <sub>A</sub> = -40 to -20°C	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ $\pm 2.0\%$ $\bigcirc$ T <sub>A</sub> = +85 to +105°C $\pm 1.0\%$ $\bigcirc$ T <sub>A</sub> = -20 to +85°C $\pm 1.5\%$ $\bigcirc$ T <sub>A</sub> = -40 to -20°C
Serial array unit	UART CSI: fclk/2 (supporting 16 Mbps), fclk/4 Simplified I <sup>2</sup> C communication	UART CSI: fclk/4 Simplified I <sup>2</sup> C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

(Remark is listed on the next page.)



 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (2/5)$ 

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low <sup>Note 1</sup>		Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				8.5 Note 2	mA
	Per pin for P60 to P63				15.0 Note 2	mA	
		Total of P00 to P04, P07, P32 to	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA
		P40 to P47, P102 to P106, P120,	$2.7~V \leq EV_{DD0} < 4.0~V$			15.0	mA
			$2.4~\text{V} \leq \text{EV}_{\text{DD0}} < 2.7~\text{V}$			9.0	mA
		Total of P05, P06, P10 to P17, P30,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA
		P31, P50 to P57, P60 to P67,	$2.7~V \leq EV_{DD0} < 4.0~V$			35.0	mA
		P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 $ (\text{When duty} \leq 70\%^{\text{Note 3}}) $	$2,4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			20.0	mA
	Total of all pins (When duty ≤ 70% Note 3)				80.0	mA	
	lo <sub>L2</sub>	Per pin for P20 to P27, P150 to P156			_	0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	$2.4~V \leq V_{DD} \leq 5.5~V$			5.0	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
  - 2. Do not exceed the total current value.
  - **3.** Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins =  $(lol \times 0.7)/(n \times 0.01)$ 

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins =  $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$ 

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

# (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (Ta = -40 to $+105^{\circ}$ C, 2.4 V $\leq$ EV<sub>DD0</sub> $\leq$ V<sub>DD</sub> $\leq$ 5.5 V, Vss = EV<sub>SS0</sub> = 0 V) (2/2)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit	
Supply	I <sub>DD2</sub>	HALT	HS (high-	fih = 32 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.54	2.90	mA
current	Note 2	mode	speed main) mode Note 7		V <sub>DD</sub> = 3.0 V		0.54	2.90	mA
				fih = 24 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.44	2.30	mA
					V <sub>DD</sub> = 3.0 V		0.44	2.30	mA
				fıн = 16 MHz <sup>Note 4</sup>	V <sub>DD</sub> = 5.0 V		0.40	1.70	mA
					V <sub>DD</sub> = 3.0 V		0.40	1.70	mA
			HS (high- speed main) mode Note 7	$f_{MX} = 20 \text{ MHz}^{Note 3},$	Square wave input		0.28	1.90	mA
				V <sub>DD</sub> = 5.0 V	Resonator connection		0.45	2.00	mA
				f <sub>MX</sub> = 20 MHz <sup>Note 3</sup> ,	Square wave input		0.28	1.90	mA
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.45	2.00	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.19	1.02	mA
				V <sub>DD</sub> = 5.0 V	Resonator connection		0.26	1.10	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.19	1.02	mA
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.26	1.10	mA
			Subsystem clock operation	fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.25	0.57	μΑ
				T <sub>A</sub> = -40°C	Resonator connection		0.44	0.76	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.30	0.57	μΑ
				T <sub>A</sub> = +25°C	Resonator connection		0.49	0.76	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.37	1.17	μΑ
				T <sub>A</sub> = +50°C	Resonator connection		0.56	1.36	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.53	1.97	μΑ
				T <sub>A</sub> = +70°C	Resonator connection		0.72	2.16	μΑ
			fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.82	3.37	μΑ	
				T <sub>A</sub> = +85°C	Resonator connection		1.01	3.56	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		3.01	15.37	μΑ
				T <sub>A</sub> = +105°C	Resonator connection		3.20	15.56	μΑ
	IDD3 <sup>Note 6</sup> STOP mode <sup>Note 8</sup>		T <sub>A</sub> = -40°C				0.18	0.50	μΑ
			$T_A = +25^{\circ}C$				0.23	0.50	μΑ
			T <sub>A</sub> = +50°C			0.30	1.10	μΑ	
			T <sub>A</sub> = +70°C				0.46	1.90	μΑ
			T <sub>A</sub> = +85°C				0.75	3.30	μΑ
			T <sub>A</sub> = +105°C				2.94	15.30	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
  - 2. During HALT instruction execution by flash memory.
  - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
  - 4. When high-speed system clock and subsystem clock are stopped.
  - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
  - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
  - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$  to 32 MHz  $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$  to 16 MHz

- 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
  - 2. fin: High-speed on-chip oscillator clock frequency
  - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
  - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is  $T_A = 25^{\circ}C$

#### (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ 

Parameter	Parameter Symbol Conditions			ions	HS (high-spee	IS (high-speed main) Mode	
					MIN.	MAX.	
Transfer rate		Transmission	$4.0~V \leq EV_{DD0} \leq 5.5$			Note 1	bps
			V, $2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 1.4 \ k\Omega, \ V_b = 2.7 \ V$		2.6 Note 2	Mbps
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0$			Note 3	bps
			$V,$ $2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$		1.2 Note 4	Mbps
			2.4 V ≤ EV <sub>DD0</sub> < 3.3			Note 5	bps
		$V,$ $1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF},  R_b = 5.5 \text{ k}\Omega,  V_b = 1.6  V$		0.43 Note 6	Mbps	

**Notes 1.** The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V  $\leq$  EV<sub>DD0</sub>  $\leq$  5.5 V and 2.7 V  $\leq$  V<sub>b</sub>  $\leq$  4.0 V

Maximum transfer rate = 
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- \* This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V  $\leq$  EV<sub>DDO</sub> < 4.0 V and 2.4 V  $\leq$  V<sub>b</sub>  $\leq$  2.7 V

Maximum transfer rate = 
$$\frac{1}{\{-C_b \times R_b \times ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- \* This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



- **Notes 1.** Excludes quantization error (±1/2 LSB).
  - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
  - **3.** When  $AV_{REFP} < V_{DD}$ , the MAX. values are as follows.

Overall error: Add  $\pm 1.0$  LSB to the MAX. value when AV<sub>REFP</sub> =  $V_{DD}$ .

Zero-scale error/Full-scale error: Add  $\pm 0.05\% FSR$  to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.

Integral linearity error/ Differential linearity error: Add  $\pm 0.5$  LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.

4. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

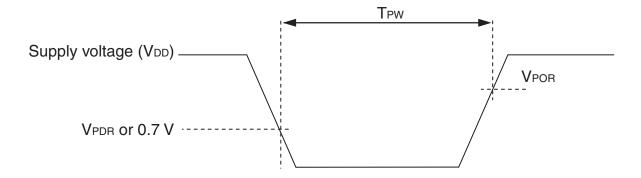


### 3.6.3 POR circuit characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.45	1.51	1.57	V
	V <sub>PDR</sub>	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width	T <sub>PW</sub>		300			μS

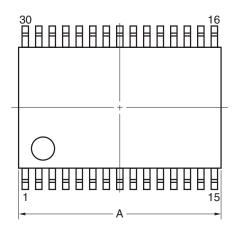
**Note** Minimum time required for a POR reset when V<sub>DD</sub> exceeds below V<sub>PDR</sub>. This is also the minimum time required for a POR reset from when V<sub>DD</sub> exceeds below 0.7 V to when V<sub>DD</sub> exceeds V<sub>POR</sub> while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).

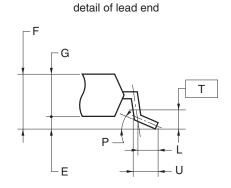


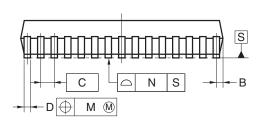
### 4.4 30-pin Products

R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AGASP R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP R5F100AAGSP, R5F100ACGSP, R5F100ADGSP, R5F100AEGSP, R5F100AFGSP, R5F100AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18

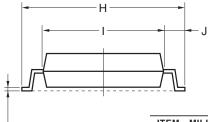






### NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.



ITEM	MILLIMETERS
Α	9.85±0.15
В	0.45 MAX.
С	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
Е	0.1±0.05
F	1.3±0.1
G	1.2
Н	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
М	0.13
N	0.10
Р	3°+5°
Т	0.25
U	0.6±0.15

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### RL78/G13 Data Sheet

			Description
Rev.	Date	Page	Summary
1.00	Feb 29, 2012	-	First Edition issued
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count
			corrected.
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.
		59, 63, 67	Descriptions of Note 8 in a table corrected.
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.
3.00	Aug 02, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution
		16 to 32	Modification of package type in 1.3.1 to 1.3.14
		33	Modification of description in 1.4 Pin Identification
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions
		55	Modification of description in table of Absolute Maximum Ratings (T <sub>A</sub> = 25°C)
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics
		57	Modification of table in 2.2.2 On-chip oscillator characteristics
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-
		68	pin products  Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-
		70	pin products  Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to
		72	100-pin products  Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-
			pin products
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		75	Modification of (4) Peripheral Functions (Common to all products)
		77	Modification of table in 2.4 AC Characteristics
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		80	Modification of figures of AC Timing Test Points and External System Clock Timing